

# SIDC81D120F6

Fast switching diode chip in EMCON-Technology

## FEATURES:

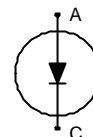
- 1200V EMCON technology 120  $\mu\text{m}$  chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

## This chip is used for:

- EUPEC power modules and discrete devices

## Applications:

- SMPS, resonant applications, drives



Chip Type	$V_R$	$I_F$	Die Size	Package	Ordering Code
SIDC81D120F6	1200V	100A	9 x 9 mm <sup>2</sup>	sawn on foil	Q67050-A4187-A001

## MECHANICAL PARAMETER:

Raster size	9 x 9	mm <sup>2</sup>
Area total / active	81 / 69.39	
Anode pad size	8.28 x 8.28	
Thickness	120	$\mu\text{m}$
Wafer size	150	mm
Flat position	180	deg
Max. possible chips per wafer	169 pcs	
Passivation frontside	Photoimide	
Anode metallisation	3200 nm AlSiCu	
Cathode metallisation	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, $\leq 500\mu\text{m}$	
Reject Ink Dot Size	$\varnothing$ 0.65mm ; max 1.2mm	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C	

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## Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}$		1200	V
Continuous forward current limited by $T_{jmax}$	$I_F$		100	A
Single pulse forward current (depending on wire bond configuration)	$I_{FSM}$	$t_P = 10\text{ ms sinusoidal}$	tbd	
Maximum repetitive forward current limited by $T_{jmax}$	$I_{FRM}$		200	
Operating junction and storage temperature	$T_j, T_{stg}$		-55...+150	°C

## Static Electrical Characteristics (tested on chip), $T_j=25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions		Value			Unit
				min.	Typ.	max.	
Reverse leakage current	$I_R$	$V_R=1200\text{ V}$	$T_j=25^\circ\text{C}$			27	$\mu\text{A}$
Cathode-Anode breakdown Voltage	$V_{Br}$	$I_R=4\text{ mA}$	$T_j=25^\circ\text{C}$	1200			V
Forward voltage drop	$V_F$	$I_F=100\text{ A}$	$T_j=25^\circ\text{C}$		2.1		V

## Dynamic Electrical Characteristics, at $T_j = 25^\circ\text{C}$ , unless otherwise specified, tested at component

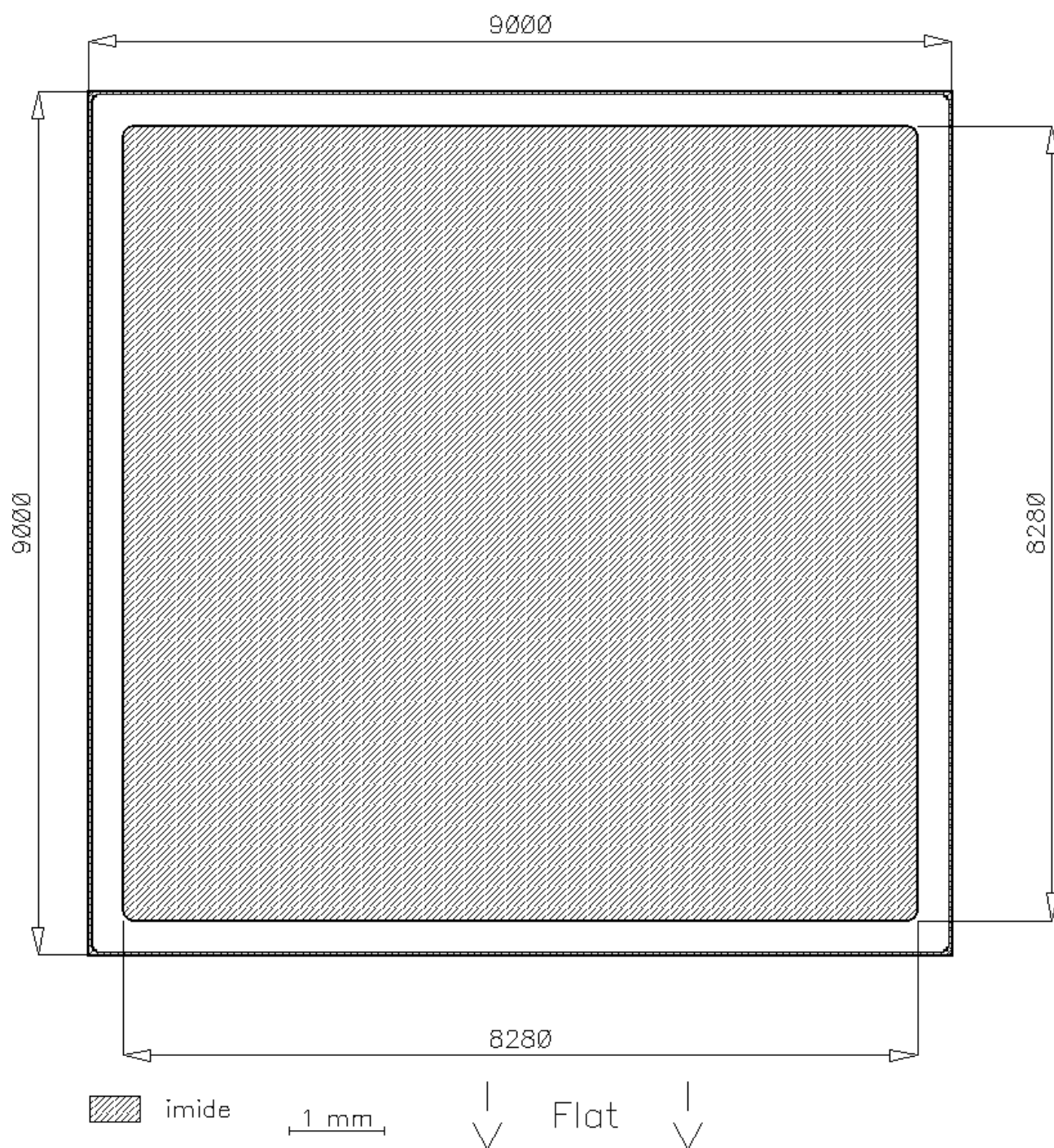
Parameter	Symbol	Conditions		Value			Unit
				min.	Typ.	max.	
Reverse recovery time	$t_{rr1}$	$I_F=100\text{ A}$	$T_j=25^\circ\text{C}$		tbd		ns
	$t_{rr2}$	$di/dt=A/ms$ $V_R=600\text{ V}$	$T_j=150^\circ\text{C}$				
Peak recovery current	$I_{RRM1}$	$I_F=100\text{ A}$	$T_j=25^\circ\text{C}$		tbd		A
	$I_{RRM2}$	$di/dt= A/ms$ $V_R= 600\text{ V}$	$T_j=150^\circ\text{C}$				
Reverse recovery charge	$Q_{rr1}$	$I_F=100\text{ A}$	$T_j=25^\circ\text{C}$		tbd		nC
	$Q_{rr2}$	$di/dt= A/ms$ $V_R= 600\text{ V}$	$T_j=150^\circ\text{C}$				
Peak rate of fall of reverse recovery current	$di_{rr1}/dt$	$I_F=100\text{ A}$	$T_j=25^\circ\text{C}$		tbd		A/ $\mu\text{s}$
	$di_{rr2}/dt$	$di/dt=A/ms$ $V_R= 600\text{ V}$	$T_j=150^\circ\text{C}$				
Softness	S1	$I_F=100\text{ A}$	$T_j=25^\circ\text{C}$		tbd		1
	S2	$di/dt= A/ms$ $V_R= 600\text{ V}$	$T_j=150^\circ\text{C}$				

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## CHIP DRAWING:

L42ØB1

Die-Size 9000 um x 9000 um



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**FURTHER ELECTRICAL CHARACTERISTICS:**

This chip data sheet refers to the device data sheet

INFINEON TECHNOLOGIES /  
EUPEC

tbd

**Description:**

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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